Abstracts

High-isolation BST-MEMS switches

Yu Liu, T.R. Taylor, J.S. Speck and R.A. York. "High-isolation BST-MEMS switches." 2002 MTT-S International Microwave Symposium Digest 02.1 (2002 Vol. I [MWSYM]): 227-230 vol.1.

In this paper, emerging (Ba,Sr)TiO/sub 3/ thin film technology was investigated for enhancing RF-MEMS capacitive switches. Materials properties of high-permittivity BST thin films and fabrication issues are discussed. Prototype BST-MEMS switches for K-/Ka-band applications were fabricated and measured. This measured data is compared with measurements from conventional SiN-based MEMS switches, showing improved isolation at lower frequencies due to the higher down-state capacitance density.

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